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ZXMD63N02X

DUAL 20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C (Notes 5 & 6)
20V	130mΩ @ V _{GS} = 4.5V	MSOP-8	2.5A
200	150mΩ @ V _{GS} = 2.7V	WISOF-6	2.3A

Features

- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

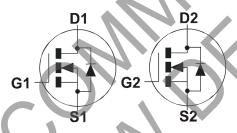
- DC-DC Converters
- Power Management Functions
- Motor Control
- Disconnect Switches

Mechanical Data

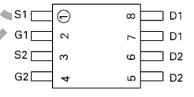
- Case: MSOP-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.0277 grams (Approximate)







Device Symbol



Top View Pin-Out

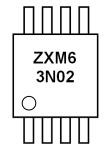
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMD63N02XTA	ZXM63N02	7	12	1,000
ZXMD63N02XTC	ZXM63N02	13	12	4,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



ZXM63N02 = Product Type Marking Code



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ZXMD63N02X

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

	Symbol	Value	Unit								
Drain-Source Voltage	Drain-Source Voltage					n-Source Voltage				20	V
Gate-Source Voltage	V_{GSS}	±12	V								
Continuous Drain Current	Steady State	$@V_{GS} = 10V; T_A = +2$ $@V_{GS} = 10V; T_A = +7$ $@V_{GS} = 10V; T_A = +1$	70°C (Notes 5 & 6)	I _D	2.5 1.9 0.78	А					
Pulsed Drain Current			(Notes 6 & 7)	I _{DM}	19	Α					
Continuous Source Current (Body Diode)			(Notes 5 & 6)	I _S	1.5	Α					
Pulsed Source Current (Body Diode)			(Notes 6 & 7)	I _{SM}	19	А					

Thermal Characteristics

Characteristic		Symbol	Value	Unit
	(Notes 6 & 8)		0.87	
Power Dissipation	(Notes 5 & 6) (Notes 8 & 9)	P_D	1.25 1.04	W
	(Notes 6 & 8)		143	
Thermal Resistance, Junction to Ambient	(Notes 5 & 6)	ReJA	100	°C/W
	(Notes 8 & 9)		120	
Thermal Resistance, Junction to Leads	(Note 10)	Rejl	84.9	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes:

- 5. For a device surface mounted on FR-4 PCB measured at $t \leq 10 \ sec.$
- 6. For device with one active die.
- 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.02, pulse width 300µs pulse width limited by maximum junction temperature.

 8. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

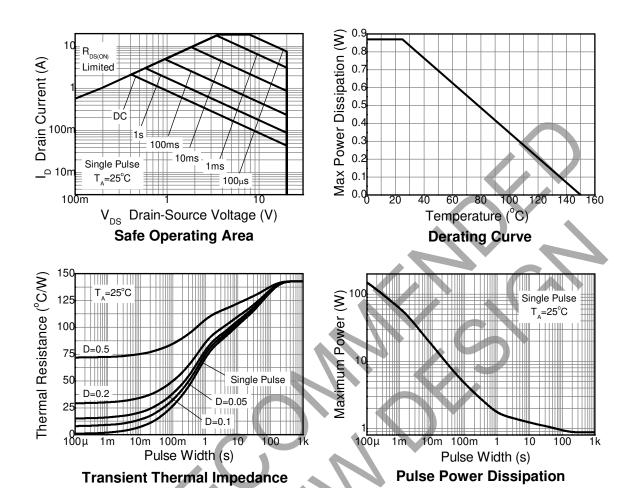
- 9. For device with two active die running at equal power.

 10. Thermal resistance from junction to solder-point (at the end of the drain lead).





Thermal Characteristics





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ZXMD63N02X

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

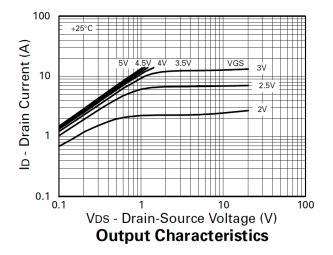
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	٧	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	0.7		3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain Source On Designation (Note 11)	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	m0	$V_{GS} = 4.5V, I_D = 1.7A$			
Static Drain-Source On-Resistance (Note 11)		$V_{GS} = 2.7V, I_D = 0.85A$				
Forward Transconductance (Notes 11 & 13)	g _{fs}	2.6		_	S	$V_{DS} = 10V, I_D = 0.85A$
Diodes Forward Voltage (Note 11)	V _{SD}	_	0.85	0.95	V	$T_J = +25$ °C, $I_S = 1.7$ A, $V_{GS} = 0$ V
DYNAMIC CHARACTERISTICS					_	
Input Capacitance (Notes 12 & 13)	C _{iss}	_	350	700		V 45444 0V
Output Capacitance (Notes 12 & 13)	Coss	_	120	250	pΕ	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance (Notes 12 & 13)	Crss	_	50	100		1 = 1.000112
Gate Resistance (Notes 12 & 13)	Rq	_	3.8	7.6	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge (Notes 12 & 13)	Qg	_	4.5	6		•
Gate-Source Charge (Notes 12 & 13)	Q_{gs}	_	0.5	0.65	nC	$V_{GS} = 4.5V, V_{DS} = 16V,$
Gate-Drain Charge (Notes 12 & 13)	Q _{gd}	_	2	2.5		$I_D = 1.7A$
Reverse Recovery Time (Note 13)	t _{RR}	_	15	30	ns	$T_J = +25^{\circ}C$, $I_F = 1.7A$,
Reverse Recovery Charge (Note 13)	Q _{RR}	_	5.9		nC	di/dt = 100A/μs
Turn-On Delay Time (Notes 12 & 13)	t _{D(ON)}		3.4			77
Turn-On Rise Time (Notes 12 & 13)	t _R	-//	8.1	_	20	$V_{DD} = 10V, I_D = 1.7A,$
Turn-Off Delay Time (Notes 12 & 13)	t _{D(OFF)}	\	13.5		ns	$R_G = 6\Omega$, $R_D = 5.7\Omega$
Turn-Off Fall Time (Notes 12 & 13)	t _F		9.1	(

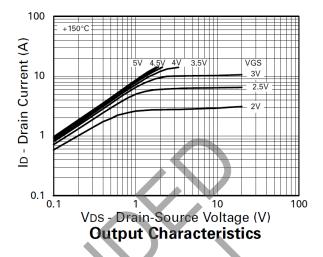
Notes:

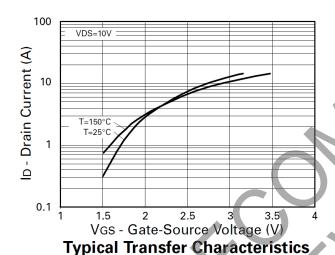
- 11. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤2%.
 12. Switching characteristics are independent of operating junction temperature.
 13. For design aid only, not subject to production testing.

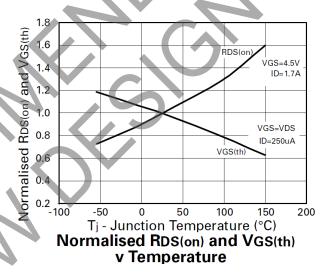


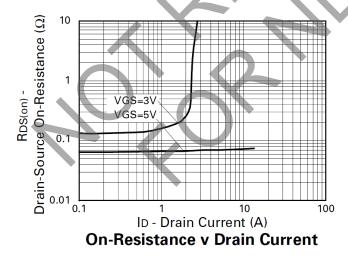
Typical Characteristics

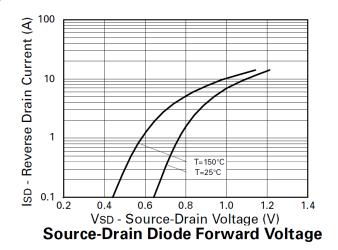






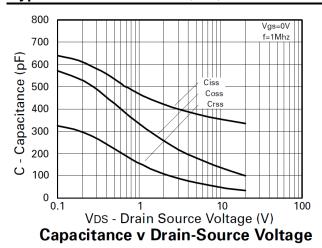


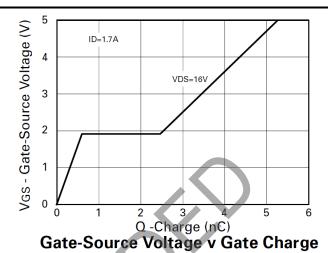




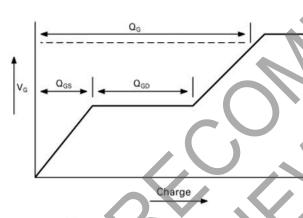


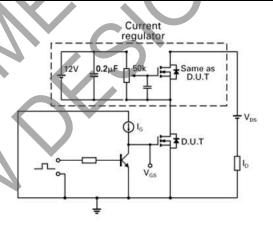
Typical Characteristics (Cont.)



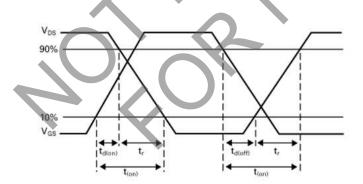


Test Circuits

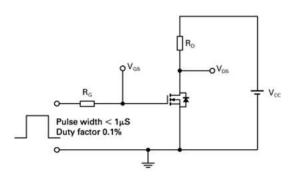




Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

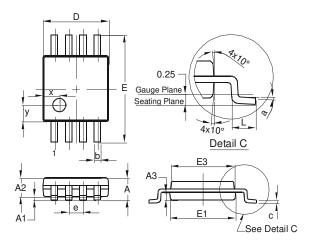
Switching time test circuit



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

MSOP-8

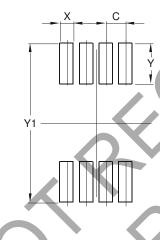


MSOP-8						
Dim	Min	Max	Тур			
Α	ı	1.10	_			
A1	0.05	0.15	0.10			
A2	0.75	0.95	0.86			
A3	0.29	0.49	0.39			
۵	0.22	0.38	0.30			
С	0.08	0.23	0.15			
D	2.90	3.10	3.00			
Е	4.70	5.10	4.90			
E1	2.90	3.10	3.00			
E3	2.85	3.05	2.95			
е	ı	ı	0.65			
L	0.40	0.80	0.60			
а	0°	8°	4°			
X	-	-	0.750			
у	-	-	0.750			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

MSOP-8



Dimensions	Value (in mm)
С	0.650
Х	0.450
Υ	1.350
V1	5 300



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ZXMD63N02X

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